



2N7002T

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	Rds(on)	I _D T _A = +25°C
60V	7.5Ω @ V _{GS} = 5V	115mA

Description and Applications

This new generation MOSFET has been designed to minimize the onstate resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- **DC-DC Converters**
- **Power Management Functions**
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

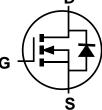
Mechanical Data

- Case: SOT523
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208@3
- Terminal Connections: See Diagram
- Weight: 0.002 grams (Approximate)

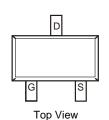




Top View







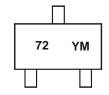
Ordering Information (Note 4)

Part Number	Case	Packaging
2N7002T-7-F	SOT523	3,000/Tape & Reel
2N7002T-13-F	SOT523	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



72 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Bate Gode Hoy												
Year	2002		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	0		Н	I	J	K	L	М	N	0	Р	R
							1					
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Chara	acteristic	Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	60	V
Drain-Gate Voltage (R _{GS} ≤ 1.0N	$M\Omega$)	VDGR	60	V
Gate-Source Voltage	Continuous Pulsed	Vgss	±20 ±40	V
Drain Current (Note 5)	Continuous Continuous @ +100°C Pulsed	l _D	115 73 800	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	PD	150	mW
Thermal Resistance, Junction to Ambient	Rеја	833	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

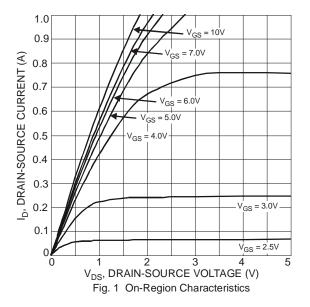
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

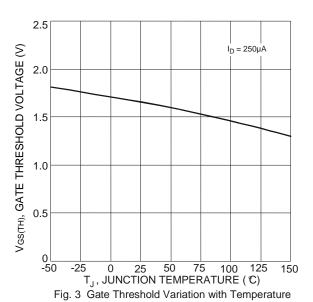
Characteristic			Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage		BVDSS	60	_	_	V	$V_{GS} = 0V, I_{D} = 10\mu A$
Zero Gate Voltage Drain Current	@ T _C = +25°C @ T _C = +125°C	IDSS	_	_	1.0 500	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Body Leakage		I _{GSS}	_	_	±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage		Vgs(th)	1.0	_	2.0	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
Static Drain-Source On-Resistance	@ T _J = +25°C			2.0	7.5	Ω	$V_{GS} = 5.0V, I_D = 0.05A$
	@ $T_J = +125$ °C	RDS(ON)		4.4	13.5	5.2	$V_{GS} = 10V, I_D = 0.5A$
On-State Drain Current		I _{D(ON)}	0.5	1.0	_	Α	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance		grs	80	_	_	mS	$V_{DS} = 10V, I_{D} = 0.2A$
DYNAMIC CHARACTERISTICS (Note	7)						
Input Capacitance		Ciss		22	50	pF	
Output Capacitance		Coss		11	25	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance			_	2.0	5.0	pF	
SWITCHING CHARACTERISTICS (Not	te 7)						
Turn-On Delay Time	•	t _{D(ON)}		7.0	20	ns	$V_{DD} = 30V, I_D = 0.2A,$
Turn-Off Delay Time		tD(OFF)		11	20	ns	$R_L = 150\Omega$, $V_{GEN} = 10V$, $R_{GEN} = 25\Omega$

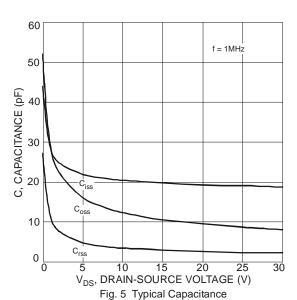
Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.6. Short duration pulse test used to minimize self-heating effect.7. Guaranteed by design. Not subject to production testing.









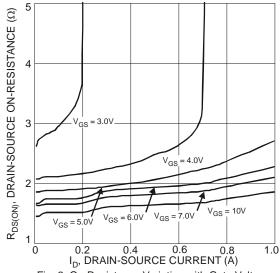


Fig. 2 On-Resistance Variation with Gate Voltage and Drain-Source Current

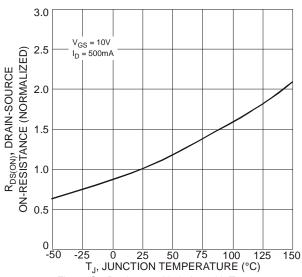
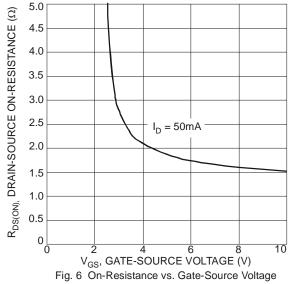


Fig. 4 On-Resistance Variation with Temperature

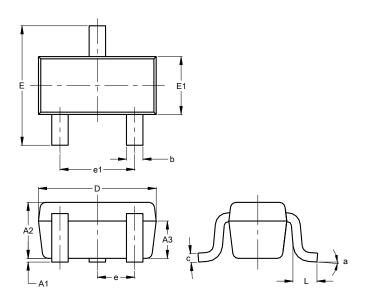




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523

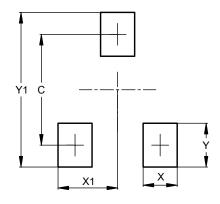


SOT523						
Dim	Min Max Typ					
A1	0.00	0.10	0.05			
A2	0.60	0.80	0.75			
A3	0.45	0.65	0.50			
b	0.15	0.30	0.22			
C	0.10	0.20	0.12			
D	1.50	1.70	1.60			
Е	1.45	1.75	1.60			
E1	0.75	0.85	0.80			
е	e 0.50 BSC					
e1	0.90	1.10	1.00			
L	0.20	0.40	0.33			
а	0°		8°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT523



Dimensions	Value (in mm)
С	1.29
Х	0.40
X1	0.70
Y	0.51
Y1	1.80



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2020, Diodes Incorporated

www.diodes.com

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Diodes Incorporated manufacturer:

Other Similar products are found below:

IRFD120 JANTX2N5237 BUK455-60A/B MIC4420CM-TR VN1206L NDP4060 SI4482DY IPS70R2K0CEAKMA1 SQD23N06-31L-GE3
TK16J60W,S1VQ(O 2SK2614(TE16L1,Q) DMN1017UCP3-7 DMN1053UCP4-7 SQJ469EP-T1-GE3 NTE2384 DMC2700UDMQ-7
DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 DMP22D4UFO-7B DMN1006UCA6-7 DMN16M9UCA6-7
STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 DMN2990UFB-7B
IPB80P04P405ATMA2 2N7002W-G MCAC30N06Y-TP MCQ7328-TP NTMC083NP10M5L NVMFS2D3P04M8LT1G BXP7N65D
BXP4N65F AOL1454G WMJ80N60C4 BXP2N20L BXP2N65D BXT1150N10J BXT1700P06M TSM60NB380CP ROG RQ7L055BGTCR
DMNH15H110SK3-13 SLF10N65ABV2 BSO203SP BSO211P